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# Peak-to-average Pumping Efficiency Improvement for Charge Pump in Phase Change Memories

Huizhang Luo, Jingtong Hu, Liang Shi, Chun Jason Xue and Qingfeng Zhuge





Oklahoma State University



香港城市大學 City University of Hong Kong



# Introduction

Increasing memory capacity requirement



NVM in main memory

PCM is one of such NVM

Challenges of DRAM

- Limited scalability, High leakage power

- Opportunities of NVM
  - High density, low leakage power, Non-volatility

# PCM in Future [ITRS 2013]

Technology	Cell size (SLC)	Read Latency	Write Latency	Write Energy
DRAM	6 F <sup>2</sup>	< 10 ns	< 10 ns	2 pJ/bit
PCM	4 F <sup>2</sup>	< 10 ns	< 50 ns	29.7 pJ/bit

Similar access latency with DRAM

Thus, PCM has similar write parallelism with DRAM.

► High write energy

Energy consumption of PCM remains a key problem.

# High Write Energy

- Much higher write voltage and current
  - RESET: 5V, 100uA,
  - SET: 3V, 50uA,
  - $V_{dd}$  1.5V for DRAM, 22uA
- Energy loss in the charge pumps (CPs)
  - Parasitic power, leakage power
  - Lead to low pumping efficiency
- Key idea
  - We improve the pumping efficiency to reduce energy consumption of PCM.





Address Bus

# Asymmetric Write in PCM



Writing a '0' requires much higher current than writing a '1'.



Write request='0000', write current requirement is high.

Write request='1111', write current requirement is low.

# PCM Charge Pump



# Pumping Efficiency [ISCA 14]

• Waste power leads to low pumping efficiency.



The pumping efficiency is a concave function of the write current [10].

#### Characteristic of a Concave Function

$$\forall_{x,y} 2f(\frac{x+y}{2}) \ge f(x) + f(y)$$



## Key Idea



1=400uA 2=200uA

**Conventional scheme** 





1=300uA 2=300uA

Uniform write current scheme



# **Problem Definition**

• The property can be extended to *num serial write current* requirements.

$$f\left(\frac{I_{1}+I_{2}+...+I_{num}}{num}\right) \ge \frac{f(I_{1})+f(I_{2})+...+f(I_{num})}{num}$$

Overall pumping efficiency can be improved if the current requirements of the *num* serial write units are uniform.

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• Average write current:

$$I_{avg} = \frac{\sum_{i=1}^{I_i} I_i}{num}$$

• Write variation:

$$WV = \frac{1}{I_{avg}} \sqrt{\frac{\sum_{i=1}^{num} (I_i - I_{avg})^2}{num - 1}}$$
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# Motivation

The write variation distribution



Fig. 5. The write variation distributions for different workloads.

The write variations are high. This motivates us to propose a write scheme to reduce write variation. Such that the pumping efficiency will be improved for energy saving.



## Peak To Average Write Scheme (PTA)

- Key idea
  - When the write units are queued in the memory controller, each write unit is divided into several subunits.
  - The sub-units are then regrouped as new write units before they are sent to the PCM chip.
- Two challenges
  - 1.how to obtain a minimal write variation during regrouping?
  - 2.What modifications of PCM chips and controller should be made?

## Challenge 1

#### • The problem:

- Assume that the current requirements of each subwrite unit *I<sub>ij</sub>* are known. The problem is to regroup the write units such that the overall write variation is minimized.
- This problem is NP-hard, which can be proved by reducing from the Subset Sum Problem.

#### – Subset Sum Problem :

 Given a set of non-negative integers, and a value sum, find the subset of the given set with sum equal to the given sum.

# IP Formulation (Off-line)

#### Objective function

- The total write variation is the minimal.

$$\min_{\mathbf{raints}} \frac{1}{I_{avg}} \sqrt{\frac{\sum_{i=1}^{num} \left(\sum_{j=1}^{M} X_{i,j} \cdot C_j - I_{avg}\right)^2}{num - 1}}$$

- Constraints I<sub>a</sub>
  - First, each sub-write must be in one and only one write group.

$$\forall_j \sum_{i=1}^{n} X_{i,j} = 1$$

- Second, each group has *sub* sub-write units.

$$\forall_i \sum_{i=1}^{num \cdot sub} X_{i,j} = sub$$

The time complexity of the IP formulation is exponential.



#### Challenge 2 Modifications of Peripheral Circuit Addr bus Simplified **PCM Chip** Column Column Row Column . . . address address address address buffer buffer buffer buffer data in . . . buffer Column Column Column decoder decoder decoder Row decode sense amp array Memo select Arravs Row



# **Experimental Setup**

- Experimental setup
  - Simulation platform: Simplescalar
- Benchmarks:
  - Mibench
- PCM configurations:

Chip	1.8V V <sub>dd</sub> , 64 concurrent RESET power buget		
Charge pump	working frequent: 133MHZ		
	RESET/SET/READ working voltages: 5/3/3V		
READ	3V, 8.4 $\mu A$ , 5.6nJ per line		
Write	RESET: 5V, 100 $\mu A$ , 29.7pJ per bit, 50ns operation latency		
	SET: 3V, 50 $\mu A$ , 22.5pJ per bit, 150ns operation latency		
PCM write unit	size: 64bit, divided into 4 sub-write units		

## Write Variations



Fig. 7. Improvement of write variations.

The write variation is reduced from 1.28 to 0.52 and 0.32 for PS and IP, respectively.

# **Pumping Efficiency**

Baseline PS IP



Fig. 8. Improvement of pumping efficiencies under various benchmarks.

PS achieves 38.8% on average while IP achieves 39.8% pumping efficiencies.

# **Energy Saving**



Fig. 9. Energy saving of memory system.

PS achieved 17.0% energy saving compared to the baseline.



# Conclusion

- We have proposed a write scheme, peak-to-average (PTA), to improve the pumping efficiencies by regrou ping the sub-write units.
- An off-line optimal Integer Programming (IP) formula tion and an online strategy, PS, are proposed to mak e the regrouping decision.
- The experimental results show that the pumping efficiency is improved from 29.8% to 38.8% by the proposed PS strategy.



# I nank you!